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November 2013

FDMC610P

P-Channel PowerTrench® MOSFET

-12 V, -80 A, 3.9 mΩ

Features

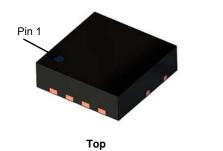
- Max $r_{DS(on)}$ = 3.9 m Ω at V_{GS} = -4.5 V, I_D = -22 A
- Max $r_{DS(on)}$ = 6.4 m Ω at V_{GS} = -2.5 V, I_D = -16 A
- State-of-the-art switching performance
- Lower output capacitance, gate resistance, and gate charge boost efficiency
- Shielded gate technology reduces switch node ringing and increases immunity to EMI and cross conduction
- RoHS Compliant

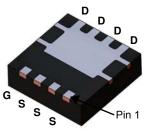
General Description

This P-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

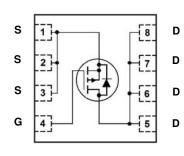
Applications

- High side switching for high end computing
- High power density DC-DC synchronous buck converter





Bottom



Power 33

MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V_{DS}	Drain to Source Voltage			-12	V
V_{GS}	Gate to Source Voltage			±8	V
	Drain Current - Continuous	T _C = 25 °C		-80	
I_D	- Continuous		(Note 1a)	-22	Α
	- Pulsed			-200	
В	Power Dissipation	T _C = 25 °C		48	W
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1a)	2.4	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	T _C = 25 °C		2.6	°C/W
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	T _A = 25 °C	(Note 1a)	53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
23AB	FDMC610P	Power 33	13 "	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	I_D = -250 μA , V_{GS} = 0 V	-12			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = -250 μA , referenced to 25 °C		-13		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -9.6 V, V _{GS} = 0 V			-1	μΑ
I_{GSS}	Gate to Source Leakage Current	V _{GS} = ±8 V, V _{DS} = 0 V			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.4	-0.7	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = -250 μA , referenced to 25 °C		3.1		mV/°C
		$V_{GS} = -4.5 \text{ V}, I_D = -22 \text{ A}$		2.8	3.9	
r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = -2.5 \text{ V}, I_D = -16 \text{ A}$		3.7	6.4	mΩ	
		$V_{GS} = -4.5 \text{ V}, I_D = -22 \text{ A}, T_J = 125 ^{\circ}\text{C}$		3.6	5.4	
9 _{FS}	Forward Transconductance	$V_{DD} = -5 \text{ V}, I_D = -22 \text{ A}$		16		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V = 6 V V = 0 V		0.89	1.25	nF
C _{oss}	Output Capacitance	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		1620	2270	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12		1440	2015	pF
R_q	Gate Resistance		0.1	3.6	7.2	Ω

Switching Characteristics

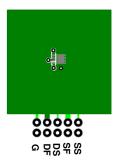
	0.4	1	
V _D 0, V _D 22.7	24	39	ns
$t_{d(off)}$ Turn-Off Delay Time $V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$	37	60	ns
	193	309	ns
t _f Fall Time	87	139	ns
Q _g Total Gate Charge	71	99	nC
Q_{gs} Gate to Source Charge $V_{DD} = -6 \text{ V}, I_D = -22 \text{ A}, V_{GS} = -4.5 \text{ V}$	13		nC
Q _{gd} Gate to Drain "Miller" Charge	14		nC

Drain-Source Diode Characteristics

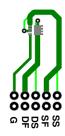
V _{SD} Source to Drain Diode Forward Voltage	Source to Drain Diode Fenyard Voltage	$V_{GS} = 0 \text{ V}, I_S = -2 \text{ A}$ (No	A (Note 2)	-0.6	-1.2	V
	$V_{GS} = 0 \text{ V}, I_S = -22 \text{ A}$ (No	ote 2)	-0.8	-1.2	V	
t _{rr}	Reverse Recovery Time			36	58	ns
Q _{rr}	Reverse Recovery Charge			19	33	nC

Note:

¹ R_{0JA} is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b. 125 °C/W when mounted on a minimum pad of 2 oz copper

^{2.} Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.

Typical Characteristics T_J = 25 °C unless otherwise noted

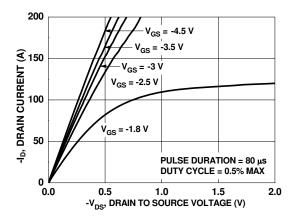


Figure 1. On Region Characteristics

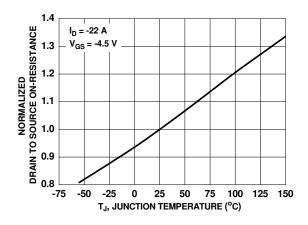


Figure 3. Normalized On Resistance vs Junction Temperature

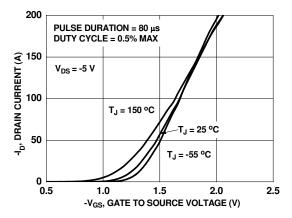


Figure 5. Transfer Characteristics

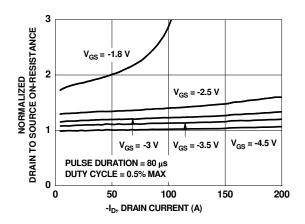


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

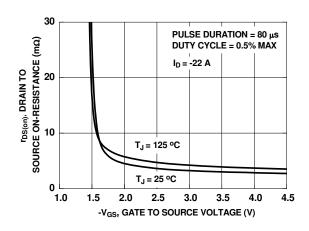


Figure 4. On-Resistance vs Gate to Source Voltage

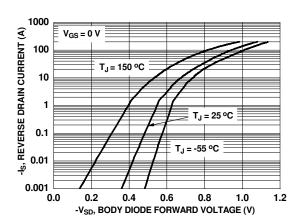


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

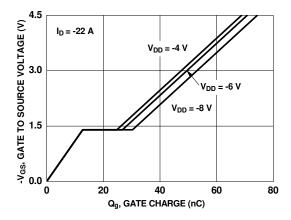


Figure 7. Gate Charge Characteristics

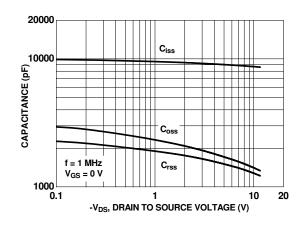


Figure 8. Capacitance vs Drain to Source Voltage

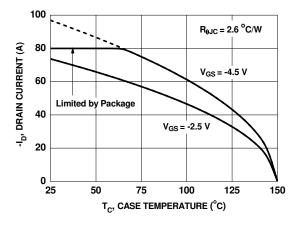


Figure 9. Maximum Continuous Drain Current vs Case Temperature

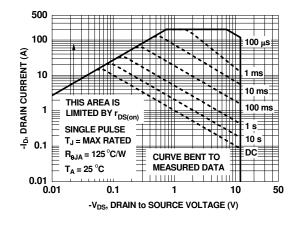


Figure 10. Forward Bias Safe Operating Area

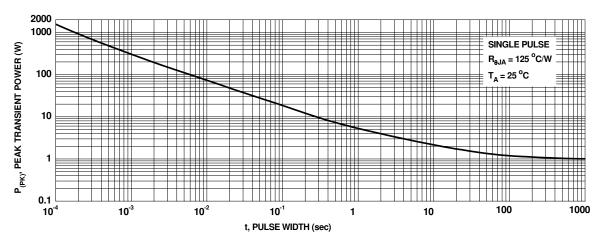


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

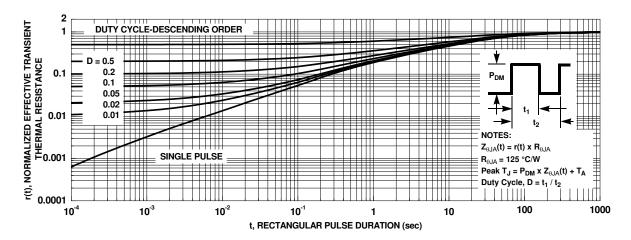
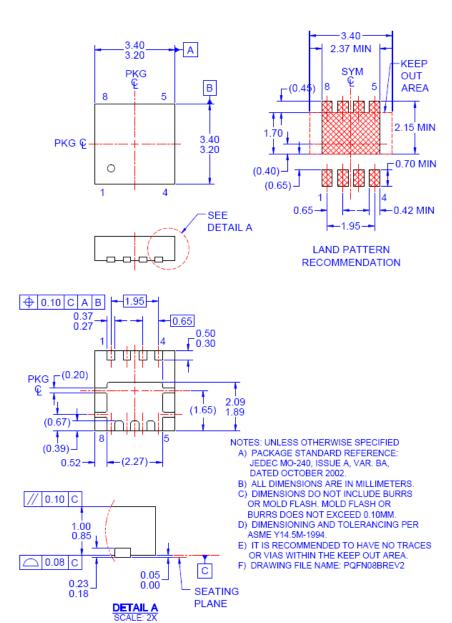


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout







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